60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI5060-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	25mΩ @ V_{GS} = 10V	32A
	40mΩ @ V_{GS} = 4.5V	25A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching—Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$—Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

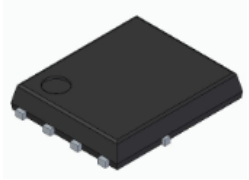
Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

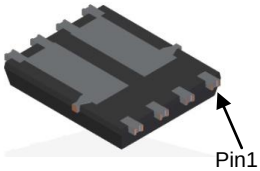
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

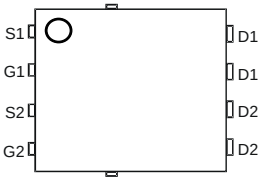
- Case: PowerDI® 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)



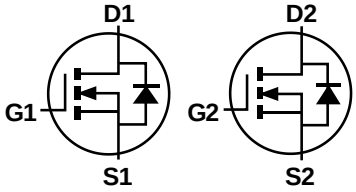
Top View



Bottom View



Pin Out
Top View



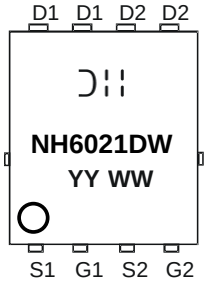
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6021SPDWQ-13	PowerDI5060-8 (SWP) (Type R)	2500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
NH6021DW = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 19 = 2019)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	T_A = +25°C T_A = +70°C	I_D	8.2 6.5	A
Continuous Drain Current (Note 8) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	32 22	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)		I_{DM}	80	A
Maximum Continuous Body Diode Forward Current (Note 7)		I_S	32	A
Avalanche Current, L = 0.1mH (Note 9)		I_{AS}	35	A
Avalanche Energy, L = 0.1mH (Note 9)		E_{AS}	64	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\Theta JA}$	99	°C/W
	t<10s		53	
Total Power Dissipation (Note 7)		P_D	2.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\Theta JA}$	54	°C/W
	t<10s		27	
Thermal Resistance, Junction to Case (Note 8)		$R_{\Theta JC}$	2.2	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	15	25	mΩ	V_{GS} = 10V, I_D = 15A
		—	21	40		V_{GS} = 4.5V, I_D = 12A
Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	V_{GS} = 0V, I_S = 2.6A
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C_{iss}	—	1,143	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	168	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	69	—	pF	
Gate Resistance	R_g	—	2.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	20.1	—	nC	V_{DS} = 30V, I_D = 20A,
Total Gate Charge (V_{GS} = 6V)	Q_g	—	12	—	nC	
Gate-Source Charge	Q_{gs}	—	4.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	5.5	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_g = 4.7Ω, I_D = 20A
Turn-On Rise Time	t_R	—	6.0	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.2	—	ns	
Turn-Off Fall Time	t_F	—	5.4	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	21.2	—	ns	I_F=20A, di/dt=100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	15.2	—	nC	

Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
8. Thermal resistance from junction to soldering point (on the exposed drain pad).
9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
10. Short duration pulse test used to minimize self-heating effect.
11. Guaranteed by design. Not subject to product testing.

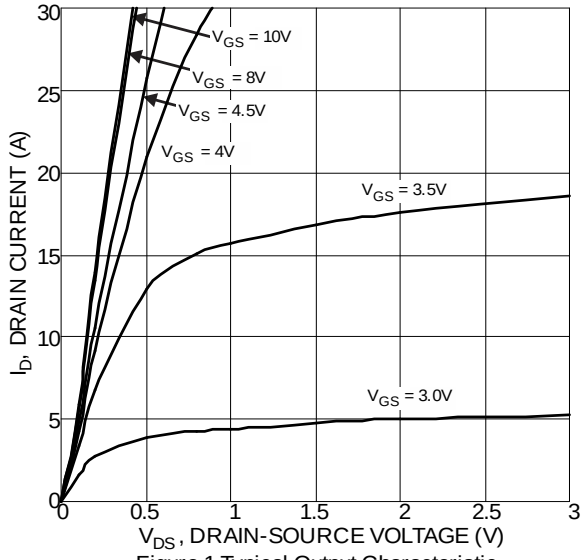


Figure 1 Typical Output Characteristic

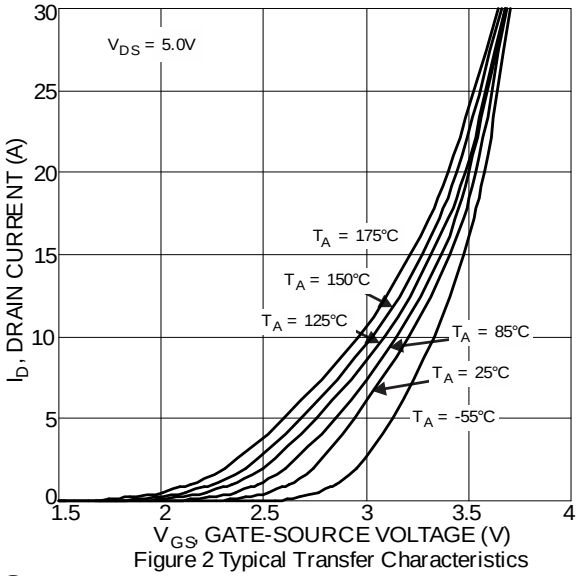


Figure 2 Typical Transfer Characteristics

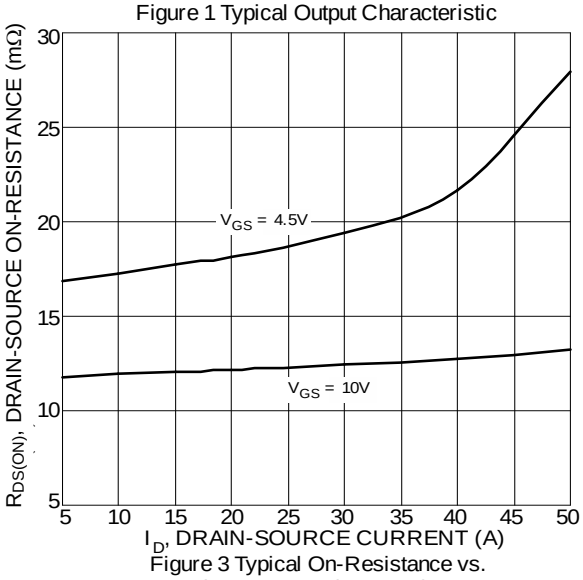


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

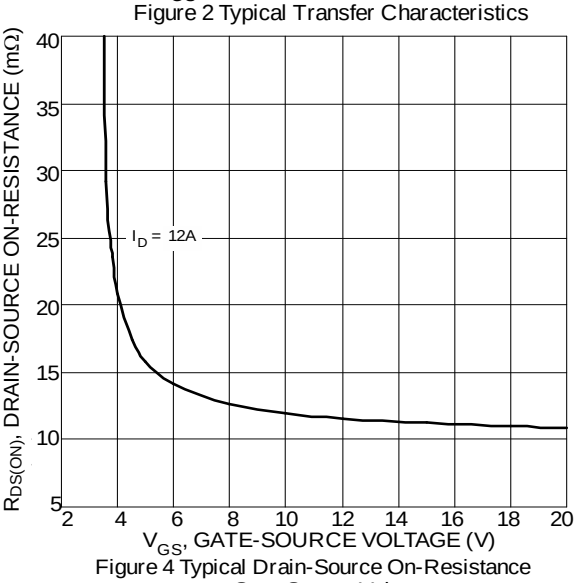


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

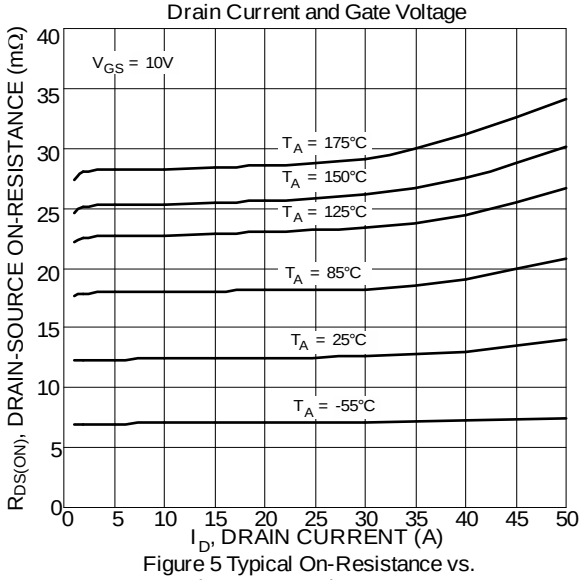


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

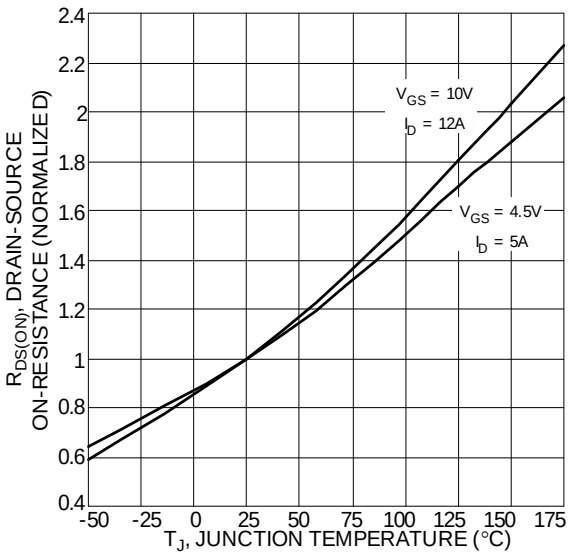


Figure 6 On-Resistance Variation with Temperature

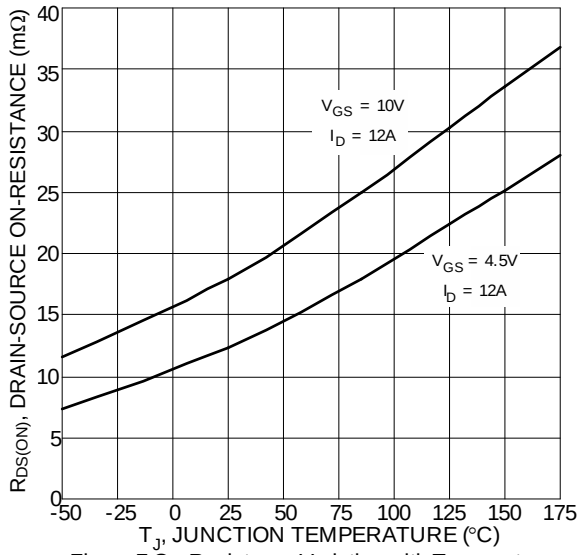


Figure 7 On-Resistance Variation with Temperature

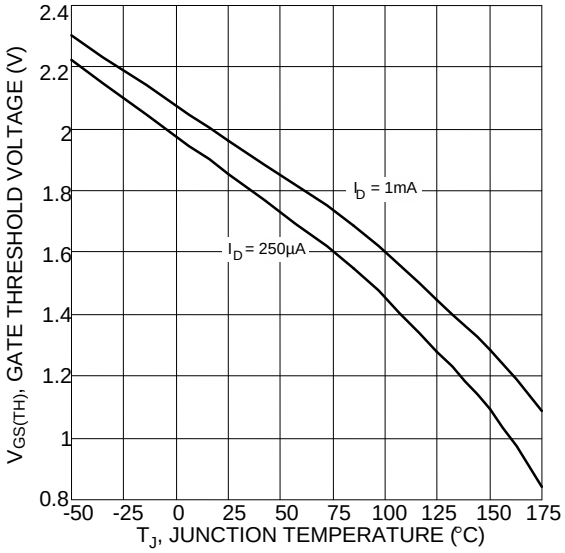


Figure 8 Gate Threshold Variation vs. Junction Temperature

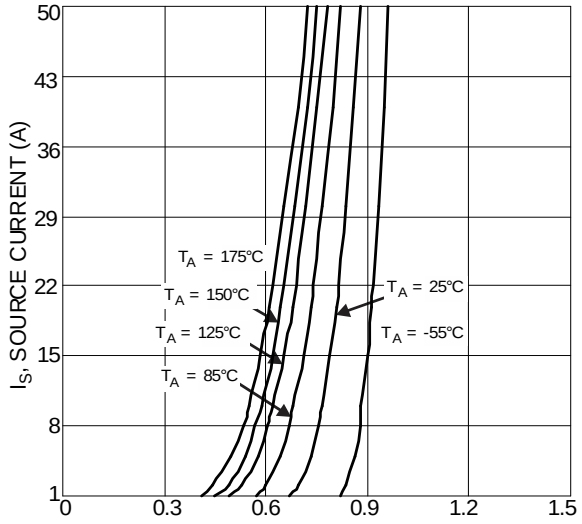


Figure 9 Diode Forward Voltage vs. Current

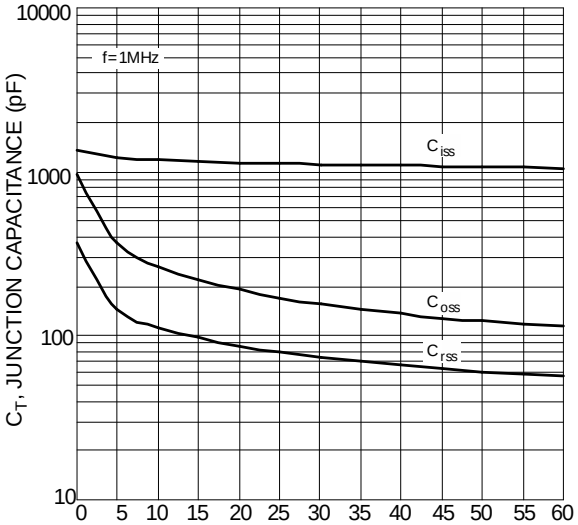


Figure 10 Typical Junction Capacitance

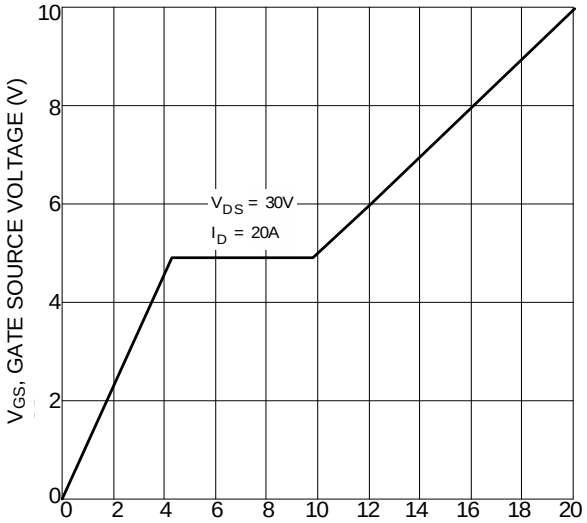


Figure 11 Gate Charge

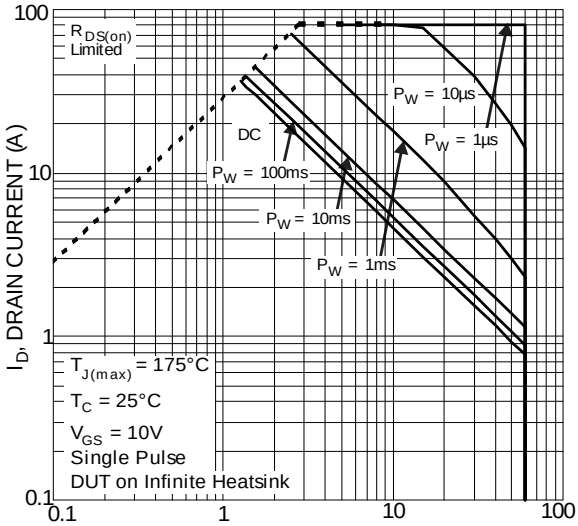


Figure 12 SOA, Safe Operation Area

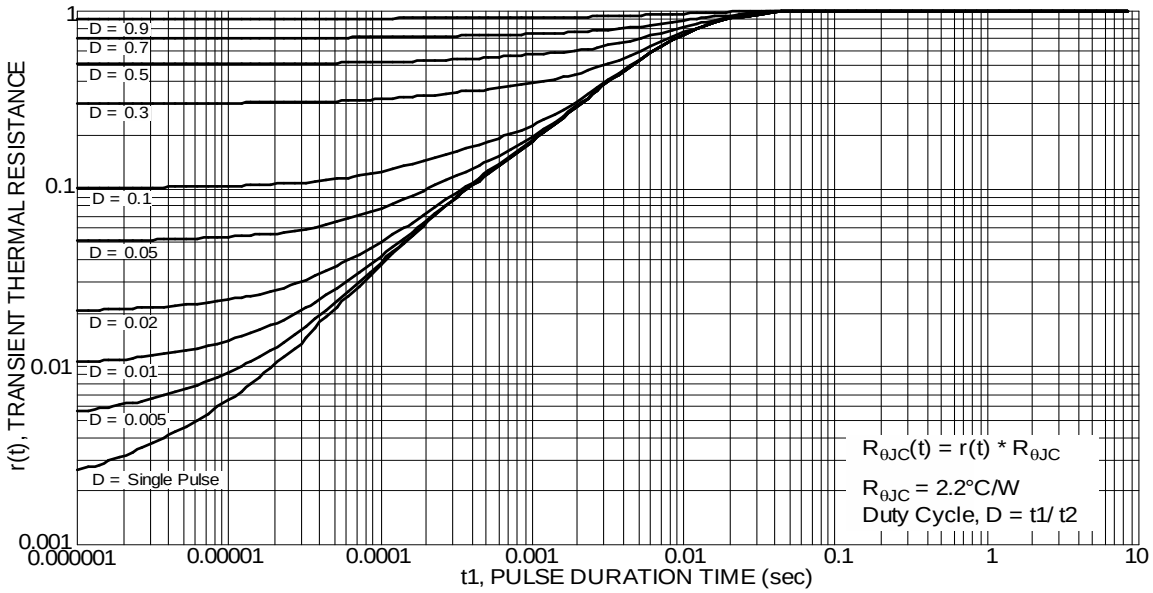
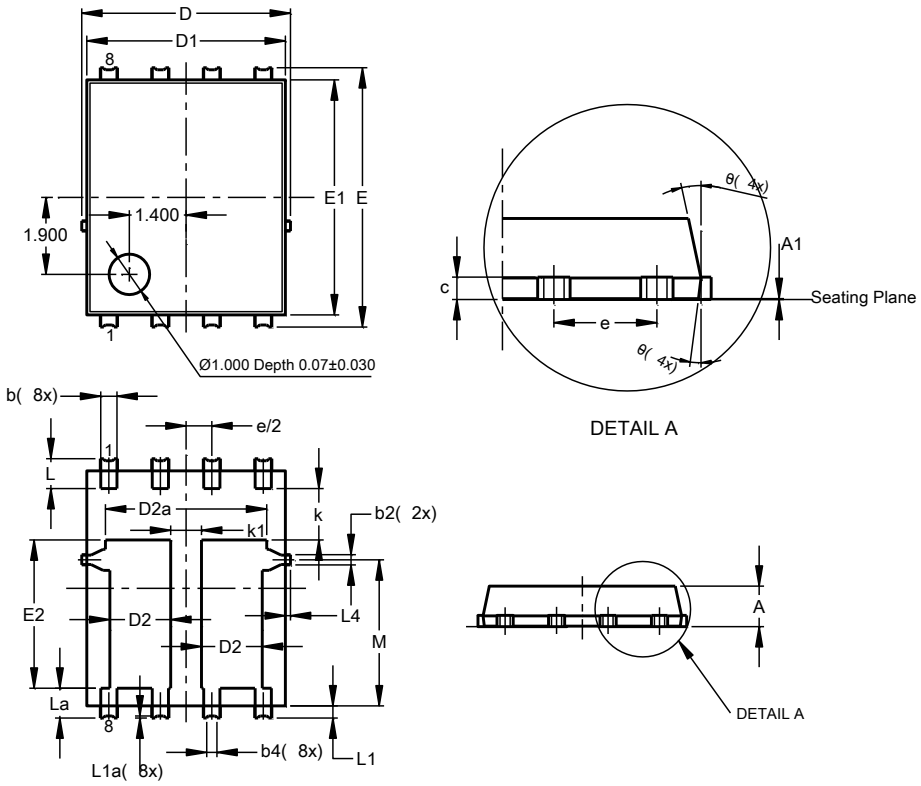


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type R)

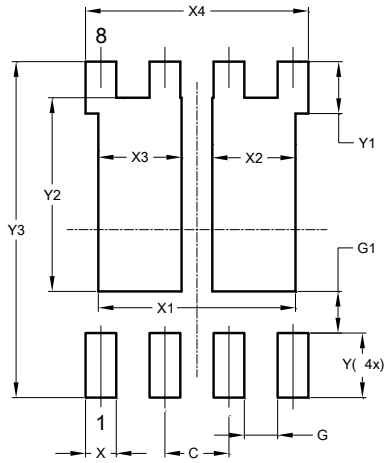


PowerDI5060-8 (SWP) (Type R)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	1.40	1.60	1.50
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
e	1.27BSC		
k	1.05	--	--
k1	0.56	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type R)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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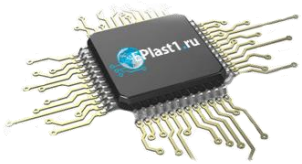
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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